

## PATENT ABSTRACTS OF JAPAN

(11)Publication number : 04-340553

(43)Date of publication of application : 26.11.1992

(51)Int.Cl.

G03F 7/11  
G09D183/00  
G03F 7/075  
G03F 7/26  
H01L 21/027

(21)Application number : 03-139459

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(22)Date of filing : 16.05.1991

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## (54) LAMINATED MATERIAL FOR MULTILAYER RESIST METHOD

(57)Abstract:

PURPOSE: To form a high-precision mask pattern on a substrate by multilayer resist method by using a uniform and dense silicon oxide film as an intermediate film formed under nonaqueous condition.

CONSTITUTION: A mask pattern is formed on a substrate to be worked by multilayer resist method that a flattening film, intermediate film, and resist film are successively formed on the substrate or an intermediate film and resist film are successively formed on the substrate and then a desired pattern is transferred successively from the upper layer. In this method, a silicon oxide film formed under nonaqueous condition is used as the intermediate film.

## LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]